

One nanometer HfO₂-based ferroelectric tunnel junctions on silicon

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In ferroelectric materials, spontaneous symmetry breaking leads to a switchable electric polarization, which offers significant promise for nonvolatile memories¹. In particular, ferroelectric tunnel junctions (FTJs) have emerged as a new resistive switching memory which exploit polarization-dependent tunnel current across a thin ferroelectric barrier²⁻⁵. Here we demonstrate FTJs with CMOS-compatible Zr-doped HfO₂ (Zr:HfO₂) ferroelectric barriers of just 1 nm thickness, grown by atomic layer deposition on silicon. These 1 nm Zr:HfO₂ tunnel junctions exhibit large polarization-driven electroresistance (19000 %), the largest value reported for HfO₂-based FTJs. In addition, due to just a 1 nm ferroelectric barrier, these junctions provide large tunnel current (> 1 A cm⁻²) at low read voltage, orders of magnitude larger than reported thicker HfO₂-based FTJs⁶. Therefore, our proof-of-principle demonstration provides an approach to simultaneously overcome three major drawbacks of prototypical FTJs: a Si-compatible ultrathin ferroelectric, large electroresistance, and large read current for high-speed operation⁷.

Ferroelectric materials are of great technological interest for low-power logic transistors^{8–11} and nonvolatile memories¹ due to collectively-ordered electrical dipoles whose polarization can be switched under an applied voltage¹². Most ferroelectric research has traditionally focused on perovskite-structure oxides¹³. Perovskites however, suffer from various chemical, thermal, lattice, and interfacial oxide incompatibilities with silicon and modern semiconductor processes¹⁴. Since the discovery of ferroelectricity in HfO₂-based thin films in 2011¹⁵, fluorite-structure binary oxides have attracted considerable interest as they are compatible with complementary metal-oxide-semiconductor (CMOS) processes¹⁶. Accordingly, HfO₂-based ferroelectric memory has received significant attention in recent years^{1,16}, primarily focused on charge-based ferroelectric random access memory (FeRAM) and ferroelectric field effect transistors (FeFETs)¹⁷. Meanwhile, resistive-switching materials – which exhibit electrically-induced resistance changes in metal–dielectric–metal junctions – have emerged as promising candidates for novel beyond-CMOS data-centric computing paradigms^{7,18,19}. In this context, ferroelectric tunnel junctions (FTJs) present a promising energy-efficient resistive switching memory^{7,19,20} as FTJs exploit the ferroic polarization functionality of the insulating barrier². Voltage-controlled polarization-dependent tunneling through the ferroelectric layer (tunnel electroresistance, TER) can yield much larger ON/OFF conductance ratios^{3,4} than, for example, current-controlled magnetic tunnel junctions¹⁹, another two-terminal tunneling resistive switching device.

A critical requirement for FTJs is to achieve a sufficiently high tunneling current (J_{on}) at the ON state to ensure that a scaled device can be read rapidly, while still exhibiting a large TER ($(J_{on} - J_{off})/J_{off} \times 100\%$)⁷. Considering the large band gap of HfO₂ (~ 6 eV), this means that the thickness of HfO₂ in the FTJ will need to be reduced to the ultrathin limit. Tunnel junctions implementing CMOS-compatible HfO₂-based ferroelectric barriers have been recently demonstrated^{21–23}, but even three nanometer Zr-doped HfO₂ (Zr:HfO₂) barriers were found to be too thick to obtain nano-ampere level current in micron-sized capacitors²⁴. Here, we demonstrate FTJs utilizing 1 nm Zr:HfO₂ as the ferroelectric barrier, grown by atomic layer deposition (ALD) directly on silicon, thereby scaling down the tunnel barrier thickness almost to the nanoscale limit. We recently demonstrated robust ferroelectricity in such 1 nm thick Zr:HfO₂ films²⁵. Additionally, we showed

that, opposing conventional scaling trends observed in perovskite ferroelectrics, ferroelectricity is enhanced rather than suppressed with decreasing thickness in Zr:HfO₂²⁵. Accordingly, FTJs employing these 1 nm Zr:HfO₂ tunnel junctions exhibit large polarization-driven TER (19000%), the largest reported for HfO₂-based FTJs (Fig. 4, Extended Data Fig. 1). In addition, these FTJs demonstrate large tunnel current ($J_{on} > 1 \text{ A cm}^{-2}$ at low read voltage), orders of magnitude larger than reported thicker HfO₂-based FTJs^{22,23} (Fig. 4). The demonstration of robust FTJ operation with the ferroelectric barrier scaled down almost to the physical limit and simultaneous occurrence of large TER and large tunnel current show potential for the eventual adoption of HfO₂-based FTJs for ultra-scaled memory applications.

One nanometer films of Zr:HfO₂ are grown by 10 cycles of ALD (4:1 Hf:Zr cycle ratio) on highly-doped silicon wafers (10^{19} cm^{-3}), buffered with approximately one nanometer chemically-grown SiO₂, and capped with 50 nm W metal (Fig. 1a). For reference, 10 ALD cycles correspond to approximately 10 Å thickness, as confirmed by synchrotron x-ray reflectivity (XRR, Extended Data Fig. 2a) and extensively characterized in our previous work on ultrathin Zr:HfO₂ films²⁵. Post-deposition annealing at 500°C with W capping is required to stabilize the ferroelectric orthorhombic phase (Pca2₁) via confinement strain²⁵ rather than the other nonpolar fluorite-structure polymorphs. Synchrotron x-ray characterization of these 1 nm Zr:HfO₂ films confirms the presence of the polar orthorhombic structure and highly-oriented films via in-plane grazing incidence diffraction (GID, Extended Data Fig. 2b) and two-dimensional reciprocal space maps (Extended Data Fig. 2c), respectively.

To establish polarization switching in 1 nm Zr:HfO₂-based capacitors (Fig. 1a), piezoresponse force microscopy (PFM) switching spectroscopy demonstrate the presence of 180° phase hysteresis (Fig. 1b), consistent with ferroelectricity. More detailed advanced scanning probe characterization previously demonstrated ferroelectricity these 1 nm Zr:HfO₂ films²⁵. Pulsed current-voltage (I - V_{write}) measurements (Fig. 1c) - applying the same waveform structure as PFM spectroscopy - demonstrate saturating, abrupt hysteretic behavior, with consistent coercive (switching) voltage as the PFM phase loops, again characteristic of polarization-driven

switching²⁶. Notably, the presence of closed hysteresis likely precludes ionic-driven mechanisms, which have been reported to result in open $I-V_{write}$ loops in HfO₂-based junctions²⁷, potentially due to irreversible oxygen vacancy migration. The lack of a forming step at high voltage required to observe resistive hysteretic switching also renders ionic-driven filamentary mechanisms unlikely. To further eliminate potentially confounding contributions in the 1 nm Zr:HfO₂ FTJs, voltage polarity-dependent pulsed $I-V$ measurements (Fig. 1c) demonstrate a resistive hysteresis sense independent of the sweep direction, inconsistent with filament formation in electrochemical resistive switching, and consistent polarization-driven resistive switching (Methods). The observed counter-clockwise $I-V_{write}$ hysteresis sense can be explained by polarization-induced barrier height modulation in the metal-ferroelectric-insulator-semiconductor (MFIS) structure (Extended Data Fig. 3). Indeed, linear $I-V_{read}$ measurements fit well to a model considering direct tunneling through a polarization-dependent trapezoidal potential barrier (Methods, Extended Data Fig. 4). Device area-independence of J_{on} (Extended Data Fig. 5) further eliminates filamentary-type mechanisms²² (Methods). Therefore, although the confounding, and often synergistic²⁷ influence of various electrochemical phenomena intertwined with polarization switching cannot be completely eliminated, multiple $I-V$ signatures in these 1 nm Zr:HfO₂ FTJs indicate minimal contributions from the relevant ionic-driven mechanisms commonly attributed to amorphous hafnia⁷. Considering the flexibility of $I-V$ measurements to provide multiple independent methods of isolating polarization-driven switching from non-ferroelectric origins, these studies indicate that $I-V$ characterization of FTJs can also serve as a diagnostic of ultrathin ferroelectricity and metrology technique for advanced nanoelectronics²⁸. $I-V$ measurements in tunnel junctions overcome shortcomings faced by conventional ferroelectric polarization-voltage ($P-V$), PFM, and synchrotron X-ray techniques by leveraging tunnel currents, disentangling competing hysteretic mechanisms, and demonstrating polarization switching, respectively (Methods).

Regarding device performance in the 1 nm Zr:HfO₂ FTJs, polarization-dependent $I-V$ measurements demonstrate ON/OFF conductance ratios approaching 200 from linear $I-V_{read}$ (Fig. 2a-c) and 100 from pulsed $I-V_{write}$ hysteresis (Fig. 2d), surpassing the previous high-mark around 50²⁹ observed for HfO₂-based FTJs (Fig. 4a, Extended Data Fig. 1). Achieving two orders of

magnitude ON/OFF conductance ratio not only surpasses all HfO₂-based FTJ literature, but also matches epitaxial perovskite-based FTJs grown by pulsed laser deposition (PLD) on silicon (Fig. 4b). Notably, J_{on} , ~ 100 nA μm^{-2} measured at low read voltage (300 mV) (Fig. 2), is orders of magnitude larger than observed in reported HfO₂-based FTJs employing thicker ferroelectric barriers^{22,23} (Fig. 4, Extended Data Fig. 1). The read voltage is well below the coercive voltage of 1 nm Zr:HfO₂, enabling non-destructive readout. The low J_{on} (< 10 nA μm^{-2}) reported for HfO₂-based FTJs – due to the lack of an ultrathin Zr:HfO₂ ferroelectric layer only recently demonstrated²⁵ – prevents practical application into highly-scaled crossbar memories due to insufficient read current⁷. Here, the 1 nm Zr:HfO₂ FTJs can maintain an ON/OFF of 10 – higher than most HfO₂-based FTJs on silicon reported thus far (Extended Data Fig. 1) – for up to 10³ cycles (Fig. 3a). Endurance cycling operates slightly below the optimal switching voltage (± 2.5 V) to prevent dielectric interlayer (SiO₂) breakdown, a common failure mechanism in HfO₂-based FeFETs¹⁷. The large TER window in these 1 nm Zr:HfO₂ FTJs affords operation at a lower voltage to enhance endurance at the slight expense of TER. This proof-of-principle 1 nm Zr:HfO₂ FTJ should motivate further work to optimize this trade-off between TER and endurance, perhaps by employing a higher- κ dielectric interlayer to improve the field-distribution through the ferroelectric. Elimination of the dielectric interlayer, e.g. depositing Zr:HfO₂ on Ge substrates without a native oxide layer, could enhance the endurance³⁰, but would likely diminish the TER without the asymmetry provided by the composite barrier³¹ (Extended Data Fig. 1). Retention measurements demonstrate the large ON/OFF window exceeding 100 can be maintained for at least 10⁴ seconds (Fig. 3b), consistent with piezoresponse retention reported in these 1 nm Zr:HfO₂ films²⁵.

Beyond the ferroelectric barrier, there are various physical mechanisms within the metal-ferroelectric-insulator-semiconductor (MFIS) structure than could potentially explain the largest observed polarization-driven TER in HfO₂-based FTJs to date. For one, MFS structures employing doped semiconductor electrodes enable barrier width modulation via the ferroelectric field effect at the dielectric-semiconductor interface. Accordingly, MFS structures have demonstrated enhanced performance in perovskite-based FTJs⁴, and even HfO₂-based FTJs on Ge³⁰ (Extended Data Fig. 1). However, barrier width modulation from the ferroelectric field-effect is not expected to be a

major contributor to the observed behavior in this work (Methods). The presence of the dielectric SiO₂ interlayer and the high silicon electrode doping level (10^{19} cm⁻³) is expected to partially screen the Zr:HfO₂ polarization from the silicon interface and result in a negligible depletion region, respectively. The dual ferroelectric-dielectric barrier present in the heterostructure is another candidate mechanism³²; recent modeling of composite barrier HfO₂-based FTJs predict depolarization fields from the dielectric interlayer to enhance the tunneling asymmetry, and therefore the TER³³. Another HfO₂-based FTJ model³¹, which combines both of the aforementioned layering effects present in our FTJ structure, found MFIS to be superior to MFIM structures due to the large asymmetry in dielectric screening between the top and bottom electrodes, which can reduce the OFF state current without diminishing the ON state current. Future HfO₂-based experimental studies should optimize composite ferroelectric-dielectric bilayers^{6,22,23,34} for FTJ performance while remaining in the ultrathin regime to maintain sufficient ON current.

Besides electrostatic effects related to the heterostructure stacking, the nature of the ultrathin ferroelectric layer itself can also contribute to the enhanced polarization-driven TER⁴. Perovskite-based FTJs have typically shown larger TER^{3,4} than reported HfO₂-based FTJs (Extended Data Fig. 1), potentially due to the enhanced ferroelectric film quality and crystallinity in high-temperature PLD-grown perovskite ferroelectric films on lattice-matched substrates⁵ compared to low-temperature ALD-grown polycrystalline films on Si. In fact, ALD-grown Zr:HfO₂ on Ge demonstrate larger TER compared to ALD-grown Zr:HfO₂ on Si³⁰, attributed to the enhanced Zr:HfO₂ ferroelectric orthorhombic phase fraction and film quality on Ge³⁰. A similar effect can be expected in these ultrathin Zr:HfO₂ films considering they are highly-oriented (Extended Data Fig. 2), in contrast to thicker polycrystalline films²⁵. Furthermore, these 1 nm Zr:HfO₂ films display enhanced ferroelectricity²⁵; the amplified polar distortions (structural gauges of polarization) in 1 nm films can increase TER considering the barrier height modulation is proportional to polarization³⁵. The common trend of diminished polarization as thickness is diminished – often observed in perovskite ferroelectrics³⁶ – does not hold for these 1 nm Zr:HfO₂ films which demonstrate "reverse" size effects²⁵. Therefore, the unique ferroelectric properties of ultrathin Zr:HfO₂²⁵ can help overcome the trade-off between high electroresistance – typically diminishes

with decreasing thickness^{4,5} – and tunnel current – increases with decreasing thickness – which have previously plagued FTJs⁴. Accordingly, the TER achieved in this work is two orders of magnitude larger than 1 nm perovskite-based FTJs on lattice-matched substrates⁵ and even matches thicker epitaxial perovskite-based ferroelectrics grown on silicon (Fig. 4b).

In summary, we have demonstrated FTJs on silicon in which the Zr:HfO₂ ferroelectric thickness has been scaled down to 1 nm, equivalent to just two fluorite-structure unit cells. These FTJs simultaneously achieve both large TER and ON current – a combination that has eluded HfO₂-based FTJs thus far (Fig. 4a, Extended Data Fig. 1). Furthermore, the data retention and endurance characteristics in these ultrathin HfO₂-based FTJs are comparable to those obtained with much thicker HfO₂-based ferroelectric layers. The ability to scale the ferroelectric thickness in an FTJ down to almost the physical thickness limit on silicon and maintain polarization-driven resistive switching offers great potential for high-density memory technology.

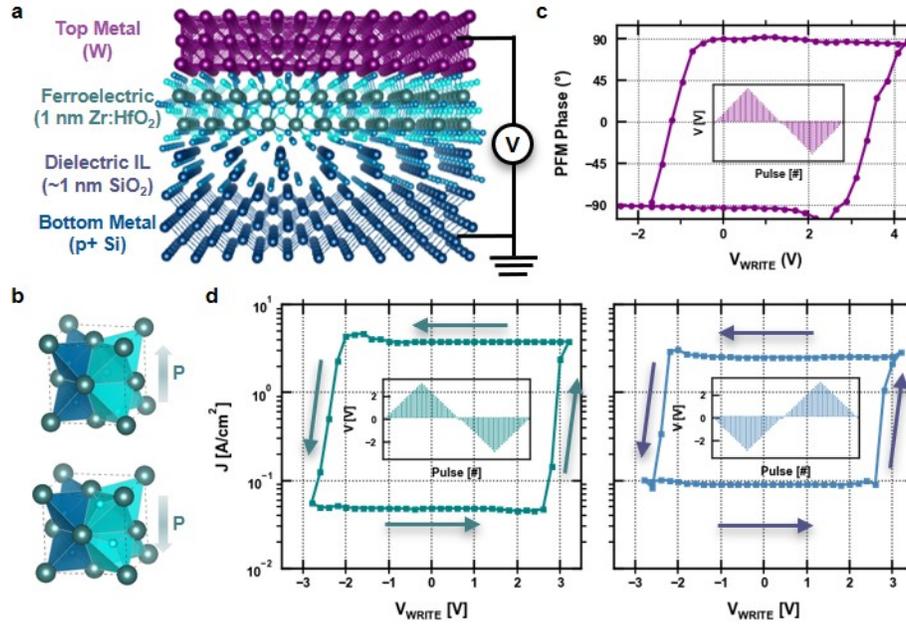


Fig. 1. Polarization-driven resistive switching in 1 nm Zr:HfO₂ junctions. (a) Schematic of the Si/SiO₂/Zr:HfO₂/W FTJ heterostructure investigated in this work, utilizing composite tunnel barriers comprised of 1 nm crystalline ferroelectric Zr:HfO₂ and 1 nm amorphous dielectric SiO₂. (b) Crystal structure schematics of the polar orthorhombic fluorite-structure ferroelectric phase (Pca₂₁), illustrating the two polarization states which dictate the resistive state in the FTJs. The different colored oxygen atoms represent the acentric oxygen atoms (cyan) and the centrosymmetric oxygen atoms (blue) within the surrounding cation (teal) tetrahedron. (c) Piezoresponse (phase) switching spectroscopy PFM loop for 1 nm Zr:HfO₂, demonstrating ferroelectric-like hysteresis. More extensive scanning probe microscopy conclusively demonstrating ferroelectricity in these 1 nm Zr:HfO₂ films is reported in our previous work²⁵. Inset: Voltage waveform used in PFM switching spectroscopy. (d) Pulsed current-voltage (I - V_{write}) hysteresis map as a function of write voltage measured at 200 mV read voltage. The abrupt hysteretic behaviour and saturating tunnelling electroresistance is characteristic of polarization-driven switching, as opposed to filamentary-based switching caused by electrochemical migration (Methods). The device demonstrates voltage polarity-independent current-voltage hysteresis sense: both

negative-positive-negative voltage polarity (left) and positive-negative-positive voltage polarity (right) demonstrate counter-clockwise hysteresis. The voltage polarity-dependent I - V hysteresis measurements further rule out filamentary-based resistive switching mechanisms and is consistent with polarization-driven switching (Methods). Inset: Voltage waveform used in the pulsed I - V_{write} measurements; the alternating sequence – staircase write, fixed read – mimics the PFM waveform. Band diagrams of the metal-ferroelectric-insulator-semiconductor (MFIS) heterostructure can explain the observed polarization-driven counterclockwise I - V_{write} hysteresis (Extended Data Fig. 3), in which positive voltage applied to W results in a lower average potential barrier height, i.e. high-current state.

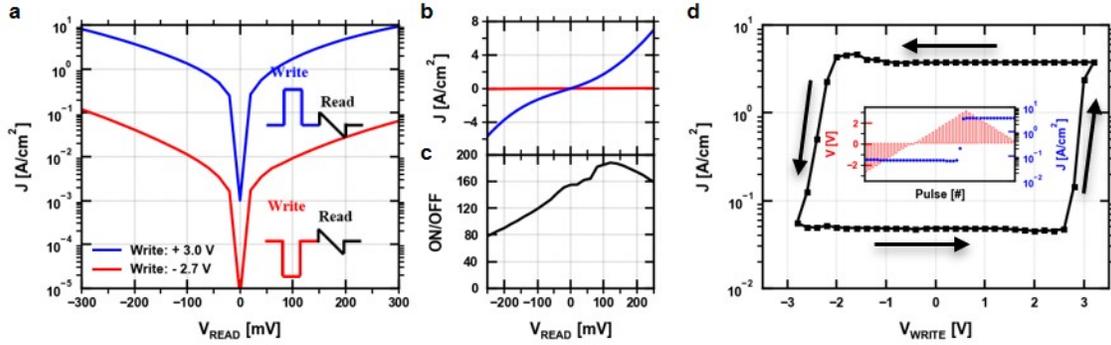


Fig. 2. Tunnel electroresistance in 1 nm Zr:HfO₂ ferroelectric tunnel junctions. (a) Linear I - V_{read} measurements after the indicated write voltage (+3.0 V, -2.7 V) was applied to set the Zr:HfO₂ polarization (FTJ current) into its respective state. The I - V_{read} data is consistent with a direct tunneling model considering polarization-dependent tunneling through a trapezoidal barrier (Methods, Extended Data Fig. 4). Inset: Schematic of voltage waveform used to write and read the FTJ current states. (b) Tunnel current as a function of read voltage in linear scale to highlight the non-linear I - V_{read} behavior. (c) Tunnel electroresistance (TER) ratio as a function of read voltage, demonstrating the maximum ON/OFF conductance ratio (190) is achieved around 150 mV. (d) Pulsed I - V_{write} hysteresis map of the read current (measured at 200 mV) as a function of write voltage (up to ± 3 V), demonstrating saturating ON/OFF conductance ratio around 100. Inset: Raw I - V measurement as a function of pulse number to highlight the two stable current states in the FTJ corresponding to the two polarization states in the 1 nm Zr:HfO₂ ferroelectric layer. The polarization-driven ON/OFF conductance ratio indicated from both steady-state (a) and pulsed (d) I - V measurements far exceed the largest ratios reported thus far in HfO₂-based FTJs on silicon (Fig. 4a) or any template (Extended Data Fig. 1), and even epitaxial perovskite-based FTJs grown on buffered silicon (Fig. 4b).

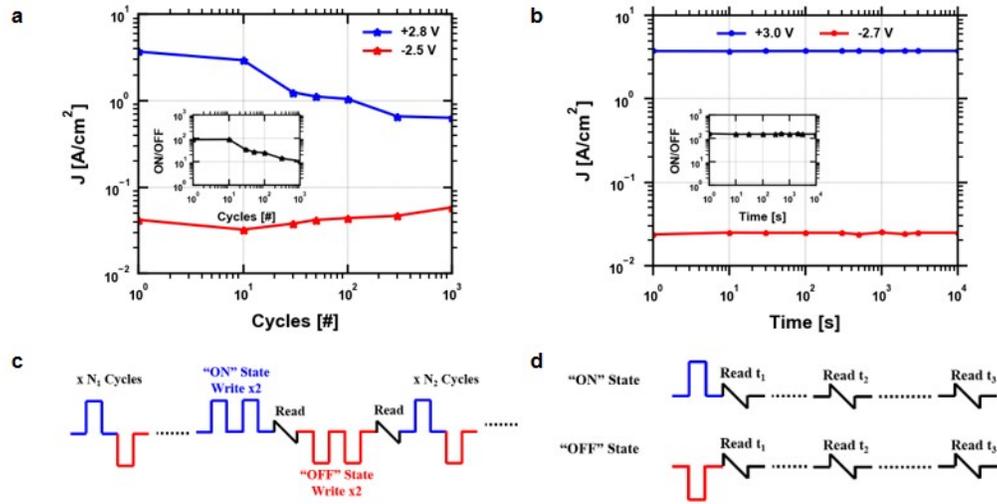


Fig. 3. Reliability of 1 nm Zr:HfO₂ ferroelectric tunnel junctions. (a) Read current (measured at 200 mV) as a function of endurance cycling (+2.8/-2.5 V write voltages) of the 1 nm Zr:HfO₂ FTJ. Inset: ON/OFF ratio as a function of write cycles, which indicates 10x ON/OFF conductance ratio is maintained up to 10³ cycles. The endurance of such a thin ferroelectric layer – considering the extensive voltage drop through the amorphous dielectric interlayer (Methods) – is enhanced by operating the FTJ at lower voltage, made possible by the large TER window. (b) Read current (measured at 200 mV) as a function of time after the FTJ is set into its respective state by the indicated write voltage (+3.0 V, -2.7 V). These retention measurements indicate the large TER can be maintained for up to 10⁴ seconds, consistent with the lack of decay in our previously-reported 1 nm Zr:HfO₂ piezoresponse retention measurements²⁵. (c), (d) Voltage waveform sequence detailing read and write steps for the endurance (c) and retention (d) measurements.

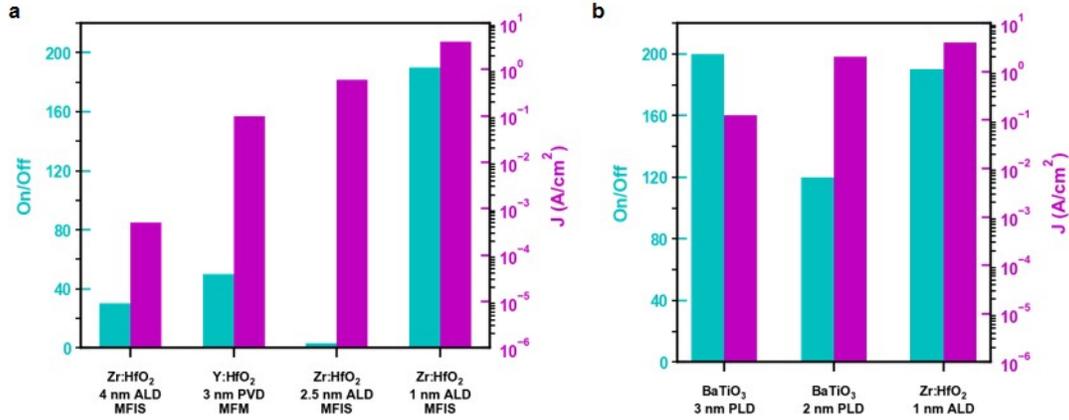


Fig. 4. Comparison to HfO₂-based and perovskite-based FTJs on Si. (a), (b) Comparison of the 1 nm Zr:HfO₂ FTJs in this work to reported HfO₂-based FTJs (a) and perovskite-based FTJs (b) grown on Si, considering polarization-driven ON/OFF conductance ratio (J_{on}/J_{off}) and current density (J_{on}). The ferroelectric barriers, thickness, deposition technique, and FTJ structure are indicated. The 1-nm Zr:HfO₂ FTJs presented in this work demonstrate the largest polarization-driven TER and current density reported thus far for HfO₂-based FTJ literature on silicon (a), across all templates beyond just silicon (Extended Data Fig. 1), and even considering epitaxial perovskite ferroelectrics grown on silicon (b). Two orders of magnitude ON/OFF conductance ratio is the typical range observed for PLD-grown epitaxial perovskite-based FTJs⁴. J_{on} is reported at 200 mV read voltage, except for the Y:HfO₂ (3 nm)²⁹ case (500 mV). For this work, J_{on} is consistent across various capacitor areas (Extended Data Fig. 5). The Y:HfO₂ (3 nm)²⁹ example is deposited by sputtering (PVD), while the Zr:HfO₂ (2.5 nm)³⁷, Zr:HfO₂ (4 nm)³⁸ and Zr:HfO₂ (1 nm, this work) ferroelectrics are deposited by the CMOS-compatible ALD technique. The BaTiO₃ (2 nm)³⁹ and BaTiO₃ (3 nm)⁴⁰ examples are grown by PLD on thick perovskite-buffered Si/SiO_x (SrTiO₃ perovskite transition layer, La_{1-x}Sr_xMnO₃ bottom electrode), which would prevent vertical-scaling, as well as introduce other CMOS-compatibility issues. Both high TER and high J_{on} are required for highly-scaled FTJ application⁶, and ultrathin ferroelectric barriers enable emerging high-density three-dimensional computing architectures¹⁹.

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